

Amendment under Article 34

To: Examiner of the Patent Office, Mitsuhiro YOSHINO

1. Identification of the International Application

PCT/JP2003/012406

2. Applicant

Name: Pioneer Corporation

Address: 4-1, Meguro 1-chome, Meguro-ku, Tokyo 153-8654 Japan

Country of nationality: Japan

Country of residence: Japan

3. Agent

Name: (7911) FUJIMURA Motohiko (seal)

Address: Fujimura & Associates
Ginza-Ohno Bldg., 1-17, Tsukiji 4-chome,
Chuo-ku, Tokyo 104-0045 Japan

TEL: 03-3543-7369

FAX: 03-3545-2898

4. Item to be Amended Claims

5. Subject Matter of Amendment:

- (1) With regard to Claim 1 of Scope of claim for Patent at page 12, "A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type $\text{Al}_x\text{Ga}_{1-x-y}\text{In}_y\text{N}$ ($0 < x < 1$, $0 \leq y < 1$, $0 < x + y < 1$), an active layer, a p-type clad layer, and a p-type contact layer, comprising: a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer, wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer." is amended to "A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$), an active layer, a p-type clad layer, and a p-type contact layer, comprising: a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer, wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer."
- (2) With regard to Claim 7 of Scope of claim for Patent at pages 12-13, "A method of manufacturing a semiconductor light-emitting element having a multilayered structure constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising: an n-type contact-layer forming step of forming an n-type contact layer of n-type GaN, and a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant concentration lower than that of the n-type contact layer." is amended to "A method of manufacturing a semiconductor light-emitting element having a multilayered structure constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising: an n-type contact-layer forming step of forming an n-type contact layer of n-type GaN, and a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant

concentration lower than that of the n-type contact layer, and a clad layer forming step of forming an n-type clad layer of n-type $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$) on the crack-preventing layer.”